



## DISCRETE POWER AND SIGNAL TECHNOLOGIES

ULTRA FAST DIODE

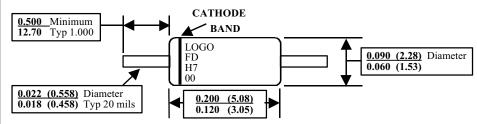
## **Information Only Data Sheet**

FINAL REVERSE CURRENT & FORWARD VOLTAGE LIMITS MIGHT BE INCREASED SLIGHTLY

## Absolute Maximum Ratings (note 1) TA = 25°C unless otherwise noted

Parameter	Value	Units
Storage Temperature	-65 to +200	°C
Maximum Junction Temperature	-65 to +175	OO
Total Power Dissipation at 25 <sup>0</sup> C	250	mW
Derate above 25 <sup>o</sup> C	1.67	mW/ <sup>o</sup> C
Working Inverse Voltage	20	V
DC Forward Current	150	mA

Note 1: These ratings are limiting values above which the serviceability of any semiconductor device may be impaired



## **Electrical Characteristics** TA = 25°C unless otherwise noted

SYM	CHARACTERISTICS	MIN	MAX	UNITS	TEST CONDITIONS
B <sub>V</sub>	Breakdown Voltage	30		V	I <sub>R</sub> = 5.0 uA
I <sub>R</sub>	Reverse Leakage		50 50	nA uA	$V_{R} = 20 V$ $V_{R} = 20 V T_{A} = 150^{\circ}C$
V <sub>F</sub>	Forward Voltage	420 520 640 760 810 0.89	500 610 740 900 990 1.25	mV mV mV mV V	$\begin{array}{rcl} I_{\rm F} &=& 10 \ {\rm uA} \\ I_{\rm F} &=& 100 \ {\rm uA} \\ I_{\rm F} &=& 1.0 \ {\rm mA} \\ I_{\rm F} &=& 10 \ {\rm mA} \\ I_{\rm F} &=& 20 \ {\rm mA} \\ I_{\rm F} &=& 50 \ {\rm mA} \end{array}$
T <sub>RR</sub>	Reverse Recovery Time		900	ps	I <sub>F</sub> = I <sub>R</sub> = 10 mA I <sub>RR</sub> = 1.0 mA R <sub>Loop</sub> = 100 Ohm
C <sub>T</sub>	Diode Capacitance		1.5	pF	V <sub>R</sub> = 0 V, f = 1.0 MHz

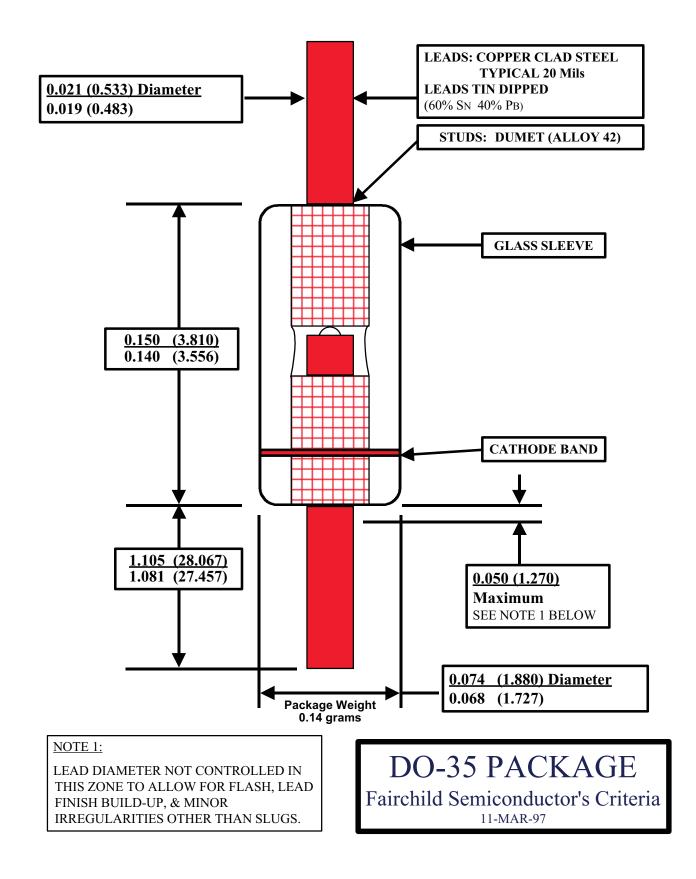


### DISCRETE POWER AND SIGNAL TECHNOLOGIES

SEMICONDUCTOR TM

STANDARD DIGITAL MARKING CRITERIA

MAXIMUM CHARACTERS PER LINE: 3 MAXIMUM NUMBER OF LINES: 4 LOGO AND CHARACTERS M & W COUNT AS 2 CHARACTERS EACH





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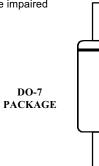
# FD700

## Ultra Fast Diode Diode

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Maximum Junction Temperature	-65 to +175	OO
Total Power Dissipation at 25 <sup>o</sup> C	250	mW
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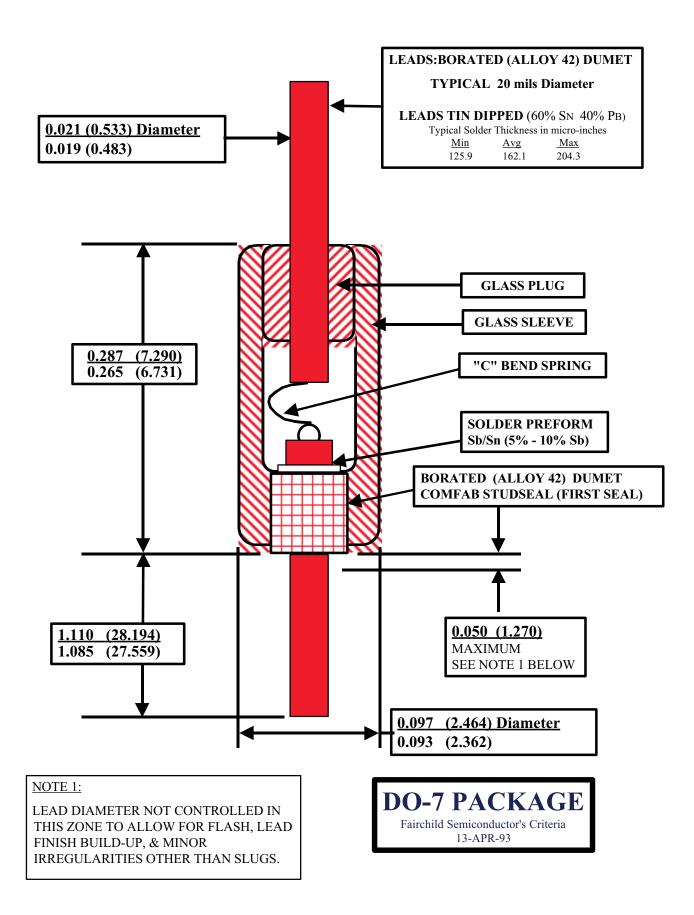


## **Electrical Characteristics** TA = 25<sup>o</sup>C unless otherwise noted

SYM	CHARACTERISTICS	MIN	MAX	UNITS	TEST CONDITIONS
$B_V$	Breakdown Voltage	30		V	I <sub>R</sub> = 5.0 uA
I <sub>R</sub>	Reverse Leakage		50 50	nA uA	$V_{R} = 20 V$ $V_{R} = 20 V T_{A} = 150^{\circ}C$
V <sub>F</sub>	Forward Voltage	420 520 640 760 810 0.89	500 610 740 880 950 1.10	mV mV mV mV V	$\begin{array}{rcl} I_{\rm F} &=& 10 \ {\rm uA} \\ I_{\rm F} &=& 100 \ {\rm uA} \\ I_{\rm F} &=& 1.0 \ {\rm mA} \\ I_{\rm F} &=& 10 \ {\rm mA} \\ I_{\rm F} &=& 20 \ {\rm mA} \\ I_{\rm F} &=& 50 \ {\rm mA} \end{array}$
T <sub>RR</sub>	Reverse Recovery Time		700	ps	I <sub>F</sub> = I <sub>R</sub> = 10 mA I <sub>RR</sub> = 1.0 mA R <sub>Loop</sub> = 100 Ohm
C <sub>T</sub>	Diode Capacitance		1.0	pF	V <sub>R</sub> = 0 V, f = 1.0 MHz







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